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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	264
Number of Logic Elements/Cells	2112
Total RAM Bits	75776
Number of I/O	38
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C
Package / Case	49-UFBGA, WLCSP
Supplier Device Package	49-WLCSP (3.11x3.19)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo3l-2100e-5uwg49ctr1k

Features

■ Solutions

- Smallest footprint, lowest power, high data throughput bridging solutions for mobile applications
- Optimized footprint, logic density, IO count, IO performance devices for IO management and logic applications
- High IO/logic, lowest cost/IO, high IO devices for IO expansion applications

■ Flexible Architecture

- Logic Density ranging from 640 to 9.4K LUT4
- High IO to LUT ratio with up to 384 IO pins

■ Advanced Packaging

- 0.4 mm pitch: 1K to 4K densities in very small footprint WLCSP (2.5 mm x 2.5 mm to 3.8 mm x 3.8 mm) with 28 to 63 IOs
- 0.5 mm pitch: 640 to 6.9K LUT densities in 6 mm x 6 mm to 10 mm x 10 mm BGA packages with up to 281 IOs
- 0.8 mm pitch: 1K to 9.4K densities with up to 384 IOs in BGA packages

■ Pre-Engineered Source Synchronous I/O

- DDR registers in I/O cells
- Dedicated gearing logic
- 7:1 Gearing for Display I/Os
- Generic DDR, DDRx2, DDRx4

■ High Performance, Flexible I/O Buffer

- Programmable sysIO™ buffer supports wide range of interfaces:
 - LVCMOS 3.3/2.5/1.8/1.5/1.2
 - LVTTTL
 - LVDS, Bus-LVDS, MLVDS, LVPECL
 - MIPI D-PHY Emulated
 - Schmitt trigger inputs, up to 0.5 V hysteresis
- Ideal for IO bridging applications
- I/Os support hot socketing
- On-chip differential termination
- Programmable pull-up or pull-down mode

■ Flexible On-Chip Clocking

- Eight primary clocks
- Up to two edge clocks for high-speed I/O interfaces (top and bottom sides only)
- Up to two analog PLLs per device with fractional-n frequency synthesis
 - Wide input frequency range (7 MHz to 400 MHz)

■ Non-volatile, Multi-time Programmable

- Instant-on
 - Powers up in microseconds
- Optional dual boot with external SPI memory
- Single-chip, secure solution
- Programmable through JTAG, SPI or I²C
- MachXO3L includes multi-time programmable NVCM
- MachXO3LF infinitely reconfigurable Flash
 - Supports background programming of non-volatile memory

■ TransFR Reconfiguration

- In-field logic update while IO holds the system state

■ Enhanced System Level Support

- On-chip hardened functions: SPI, I²C, timer/counter
- On-chip oscillator with 5.5% accuracy
- Unique TraceID for system tracking
- Single power supply with extended operating range
- IEEE Standard 1149.1 boundary scan
- IEEE 1532 compliant in-system programming

■ Applications

- Consumer Electronics
- Compute and Storage
- Wireless Communications
- Industrial Control Systems
- Automotive System

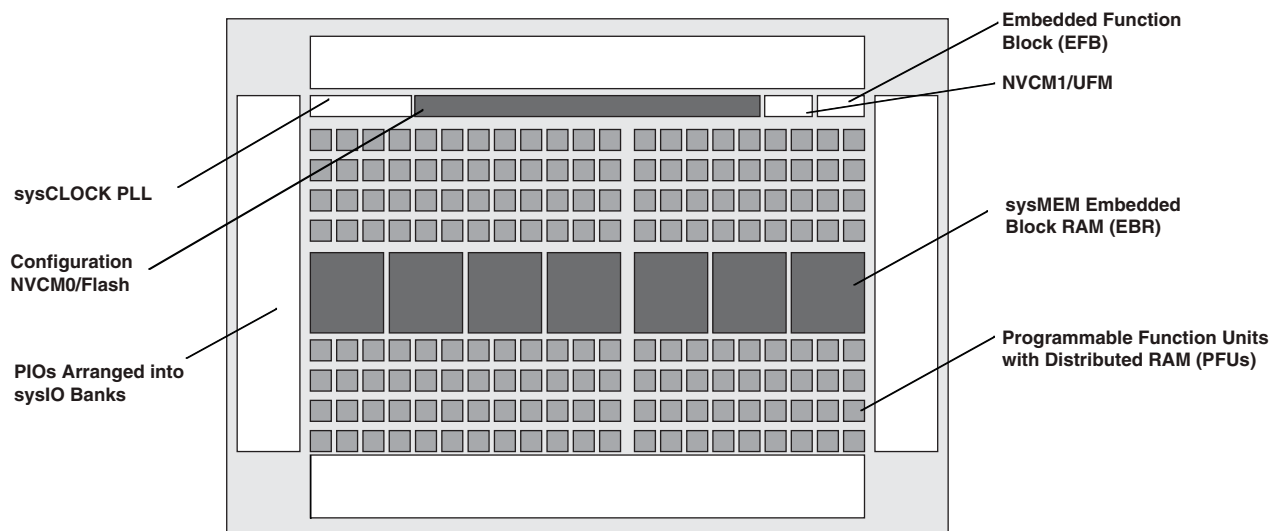
■ Low Cost Migration Path

- Migration from the Flash based MachXO3LF to the NVCM based MachXO3L
- Pin compatible and equivalent timing

Architecture Overview

The MachXO3L/LF family architecture contains an array of logic blocks surrounded by Programmable I/O (PIO). All logic density devices in this family have sysCLOCK™ PLLs and blocks of sysMEM Embedded Block RAM (EBRs). Figure 2-1 and Figure 2-2 show the block diagrams of the various family members.

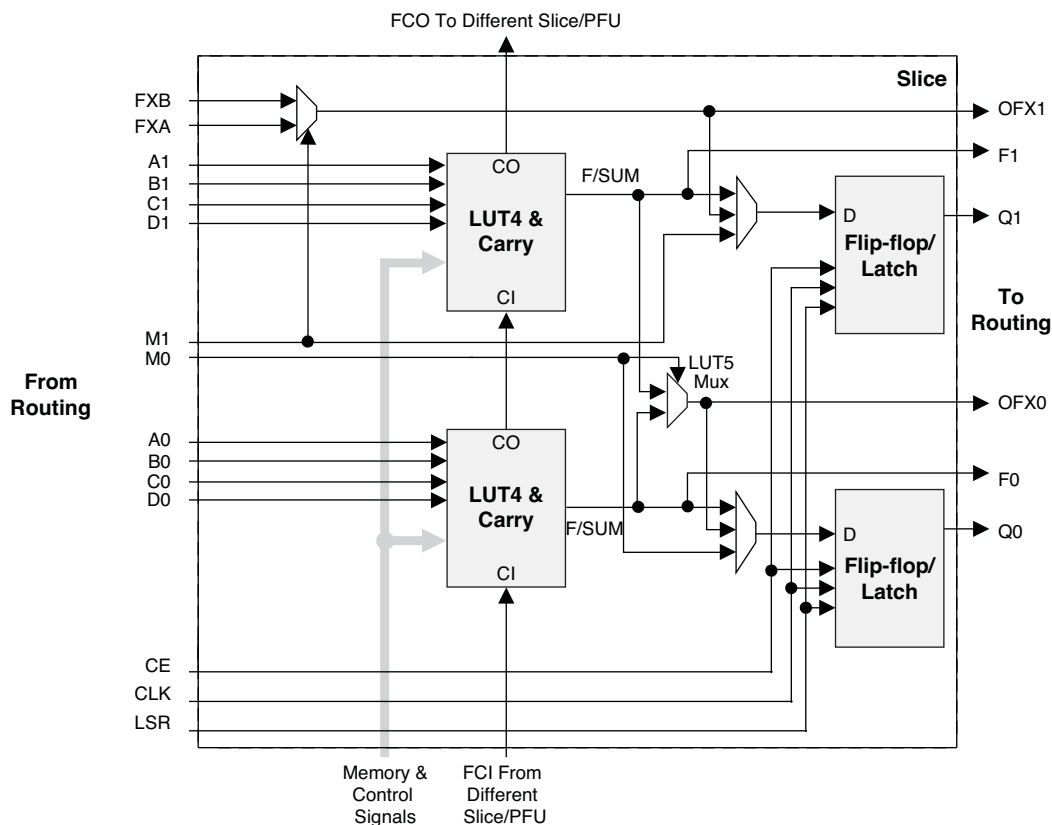
Figure 2-1. Top View of the MachXO3L/LF-1300 Device



Notes:

- MachXO3L/LF-640 is similar to MachXO3L/LF-1300. MachXO3L/LF-640 has a lower LUT count.
- MachXO3L devices have NVCM, MachXO3LF devices have Flash.

Figure 2-4. Slice Diagram



For Slices 0 and 1, memory control signals are generated from Slice 2 as follows:

- WCK is CLK
- WRE is from LSR
- DI[3:2] for Slice 1 and DI[1:0] for Slice 0 data from Slice 2
- WAD [A:D] is a 4-bit address from slice 2 LUT input

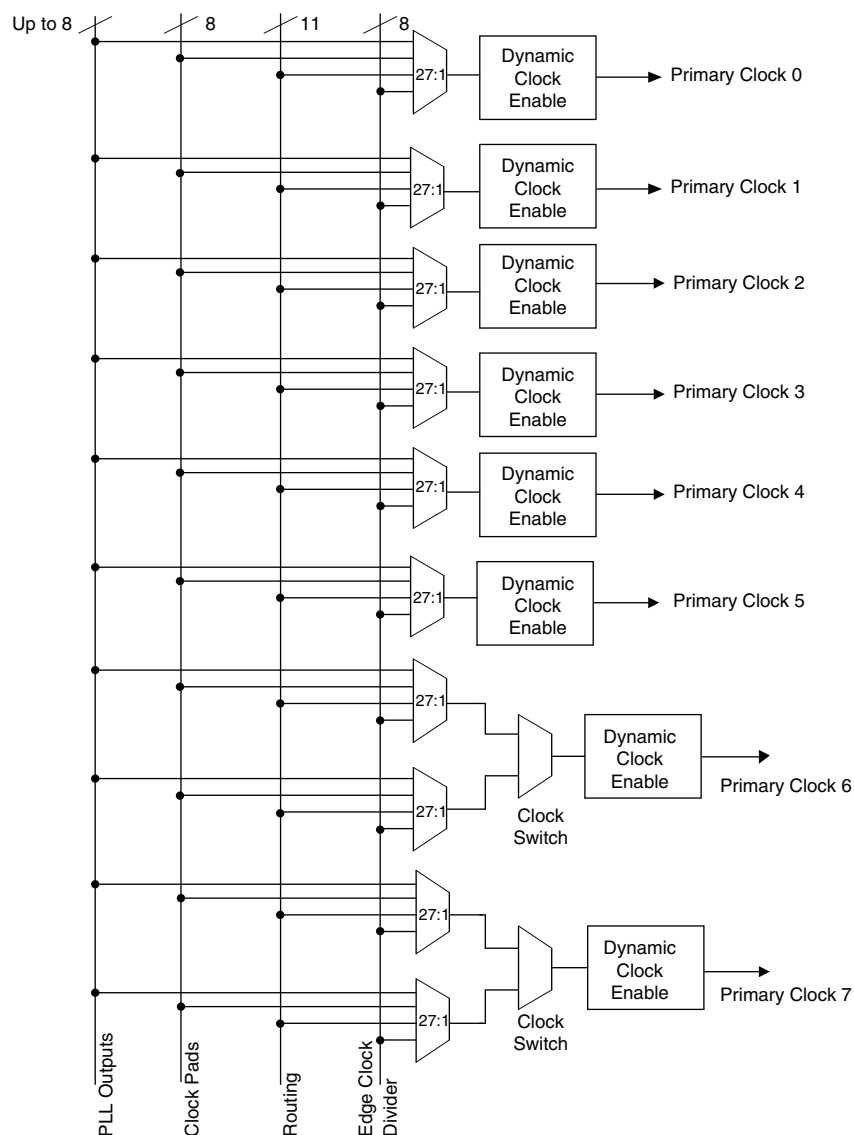
Table 2-2. Slice Signal Descriptions

Function	Type	Signal Names	Description
Input	Data signal	A0, B0, C0, D0	Inputs to LUT4
Input	Data signal	A1, B1, C1, D1	Inputs to LUT4
Input	Multi-purpose	M0/M1	Multi-purpose input
Input	Control signal	CE	Clock enable
Input	Control signal	LSR	Local set/reset
Input	Control signal	CLK	System clock
Input	Inter-PFU signal	FCIN	Fast carry in ¹
Output	Data signals	F0, F1	LUT4 output register bypass signals
Output	Data signals	Q0, Q1	Register outputs
Output	Data signals	OFX0	Output of a LUT5 MUX
Output	Data signals	OFX1	Output of a LUT6, LUT7, LUT8 ² MUX depending on the slice
Output	Inter-PFU signal	FCO	Fast carry out ¹

1. See Figure 2-3 for connection details.

2. Requires two PFUs.

Figure 2-5. Primary Clocks for MachXO3L/LF Devices



Eight secondary high fanout nets are generated from eight 8:1 muxes as shown in Figure 2-6. One of the eight inputs to the secondary high fanout net input mux comes from dual function clock pins and the remaining seven come from internal routing. The maximum frequency for the secondary clock network is shown in MachXO3L/LF External Switching Characteristics table.

Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
True Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
Pseudo Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18
FIFO	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. EBR initialization data can be loaded from the NVCM or Configuration Flash.

MachXO3LF EBR initialization data can also be loaded from the UFM. To maximize the number of UFM bits, initialize the EBRs used in your design to an all-zero pattern. Initializing to an all-zero pattern does not use up UFM bits. MachXO3LF devices have been designed such that multiple EBRs share the same initialization memory space if they are initialized to the same pattern.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Single, Dual, Pseudo-Dual Port and FIFO Modes

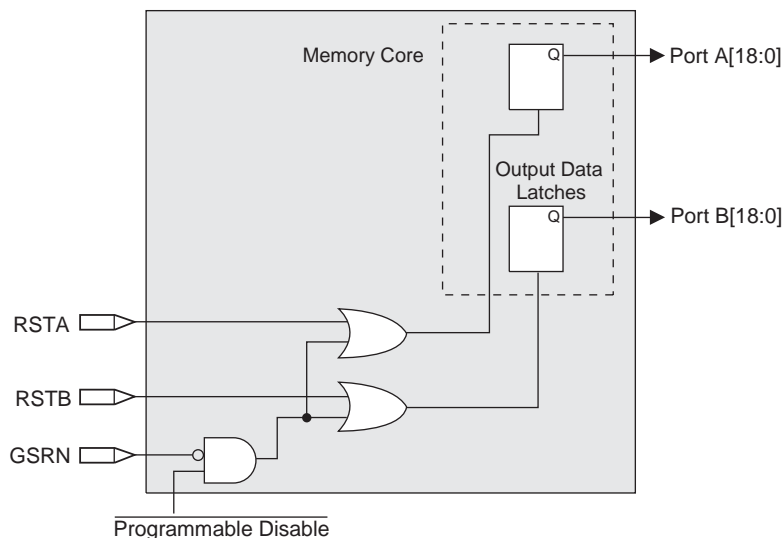
Figure 2-8 shows the five basic memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the memory array output.

state. The RPRST signal is used to reset the read pointer. The purpose of this reset is to retransmit the data that is in the FIFO. In these applications it is important to keep careful track of when a packet is written into or read from the FIFO.

Memory Core Reset

The memory core contains data output latches for ports A and B. These are simple latches that can be reset synchronously or asynchronously. RSTA and RSTB are local signals, which reset the output latches associated with port A and port B respectively. The Global Reset (GSRN) signal resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-9.

Figure 2-9. Memory Core Reset

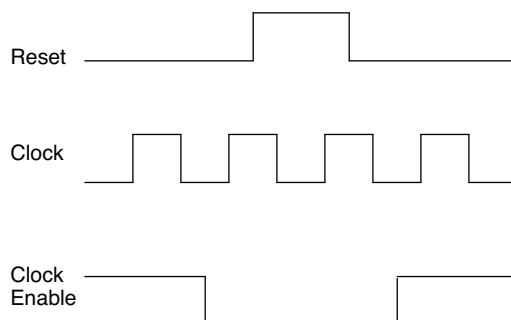


For further information on the sysMEM EBR block, please refer to TN1290, [Memory Usage Guide for MachXO3 Devices](#).

EBR Asynchronous Reset

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the reset is released, as shown in Figure 2-10. The GSR input to the EBR is always asynchronous.

Figure 2-10. EBR Asynchronous Reset (Including GSR) Timing Diagram



If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of $1/t_{MAX}$ (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

PIO

The PIO contains three blocks: an input register block, output register block and tri-state register block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

Table 2-8. PIO Signal List

Pin Name	I/O Type	Description
CE	Input	Clock Enable
D	Input	Pin input from sysIO buffer.
INDD	Output	Register bypassed input.
INCK	Output	Clock input
Q0	Output	DDR positive edge input
Q1	Output	Registered input/DDR negative edge input
D0	Input	Output signal from the core (SDR and DDR)
D1	Input	Output signal from the core (DDR)
TD	Input	Tri-state signal from the core
Q	Output	Data output signals to sysIO Buffer
TQ	Output	Tri-state output signals to sysIO Buffer
SCLK	Input	System clock for input and output/tri-state blocks.
RST	Input	Local set reset signal

Input Register Block

The input register blocks for the PIOs on all edges contain delay elements and registers that can be used to condition high-speed interface signals before they are passed to the device core.

Left, Top, Bottom Edges

Input signals are fed from the sysIO buffer to the input register block (as signal D). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), and a clock (INCK). If an input delay is desired, users can select a fixed delay. I/Os on the bottom edge also have a dynamic delay, DEL[4:0]. The delay, if selected, reduces input register hold time requirements when using a global clock. The input block allows two modes of operation. In single data rate (SDR) the data is registered with the system clock (SCLK) by one of the registers in the single data rate sync register block. In Generic DDR mode, two registers are used to sample the data on the positive and negative edges of the system clock (SCLK) signal, creating two data streams.

Input Gearbox

Each PIC on the bottom edge has a built-in 1:8 input gearbox. Each of these input gearboxes may be programmed as a 1:7 de-serializer or as one IDDRX4 (1:8) gearbox or as two IDDRX2 (1:4) gearboxes. Table 2-9 shows the gearbox signals.

Table 2-9. Input Gearbox Signal List

Name	I/O Type	Description
D	Input	High-speed data input after programmable delay in PIO A input register block
ALIGNWD	Input	Data alignment signal from device core
SCLK	Input	Slow-speed system clock
ECLK[1:0]	Input	High-speed edge clock
RST	Input	Reset
Q[7:0]	Output	Low-speed data to device core: Video RX(1:7): Q[6:0] GDDRX4(1:8): Q[7:0] GDDRX2(1:4)(IOL-A): Q4, Q5, Q6, Q7 GDDRX2(1:4)(IOL-C): Q0, Q1, Q2, Q3

These gearboxes have three stage pipeline registers. The first stage registers sample the high-speed input data by the high-speed edge clock on its rising and falling edges. The second stage registers perform data alignment based on the control signals UPDATE and SEL0 from the control block. The third stage pipeline registers pass the data to the device core synchronized to the low-speed system clock. Figure 2-13 shows a block diagram of the input gearbox.

Table 2-11 shows the I/O standards (together with their supply and reference voltages) supported by the MachXO3L/LF devices. For further information on utilizing the sysIO buffer to support a variety of standards please see TN1280, [MachXO3 sysIO Usage Guide](#).

Table 2-11. Supported Input Standards

Input Standard	VCCIO (Typ.)				
	3.3 V	2.5 V	1.8 V	1.5 V	1.2 V
Single-Ended Interfaces					
LVTTTL	Yes				
LVC MOS33	Yes				
LVC MOS25		Yes			
LVC MOS18			Yes		
LVC MOS15				Yes	
LVC MOS12					Yes
PCI	Yes				
Differential Interfaces					
LVDS	Yes	Yes			
BLVDS, MLVDS, LVPECL, RSDS	Yes	Yes			
MIPI ¹	Yes	Yes			
LVTTLD	Yes				
LVC MOS33D	Yes				
LVC MOS25D		Yes			
LVC MOS18D			Yes		

1. These interfaces can be emulated with external resistors in all devices.

There are some limitations on the use of the hardened user SPI. These are defined in the following technical notes:

- TN1087, [Minimizing System Interruption During Configuration Using TransFR Technology](#) (Appendix B)
- TN1293, [Using Hardened Control Functions in MachXO3 Devices](#)

Figure 2-19. SPI Core Block Diagram

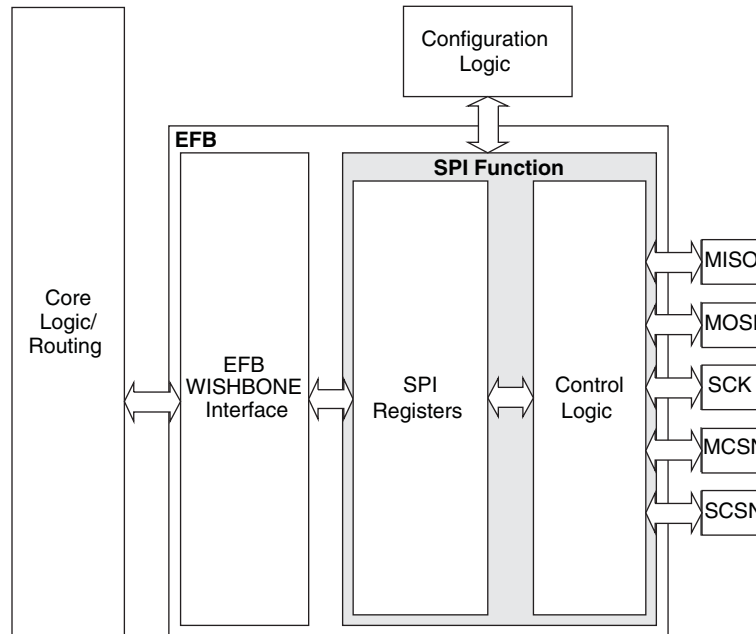


Table 2-15 describes the signals interfacing with the SPI cores.

Table 2-15. SPI Core Signal Description

Signal Name	I/O	Master/Slave	Description
spi_csn[0]	O	Master	SPI master chip-select output
spi_csn[1..7]	O	Master	Additional SPI chip-select outputs (total up to eight slaves)
spi_scsn	I	Slave	SPI slave chip-select input
spi_irq	O	Master/Slave	Interrupt request
spi_clk	I/O	Master/Slave	SPI clock. Output in master mode. Input in slave mode.
spi_miso	I/O	Master/Slave	SPI data. Input in master mode. Output in slave mode.
spi_mosi	I/O	Master/Slave	SPI data. Output in master mode. Input in slave mode.
sn	I	Slave	Configuration Slave Chip Select (active low), dedicated for selecting the Configuration Logic.
cfg_stdbv	O	Master/Slave	Stand-by signal – To be connected only to the power module of the MachXO3L/LF device. The signal is enabled only if the “Wakeup Enable” feature has been set within the EFB GUI, SPI Tab.
cfg_wake	O	Master/Slave	Wake-up signal – To be connected only to the power module of the MachXO3L/LF device. The signal is enabled only if the “Wakeup Enable” feature has been set within the EFB GUI, SPI Tab.

Hardened Timer/Counter

MachXO3L/LF devices provide a hard Timer/Counter IP core. This Timer/Counter is a general purpose, bi-directional, 16-bit timer/counter module with independent output compare units and PWM support. The Timer/Counter supports the following functions:

- Supports the following modes of operation:
 - Watchdog timer
 - Clear timer on compare match
 - Fast PWM
 - Phase and Frequency Correct PWM
- Programmable clock input source
- Programmable input clock prescaler
- One static interrupt output to routing
- One wake-up interrupt to on-chip standby mode controller.
- Three independent interrupt sources: overflow, output compare match, and input capture
- Auto reload
- Time-stamping support on the input capture unit
- Waveform generation on the output
- Glitch-free PWM waveform generation with variable PWM period
- Internal WISHBONE bus access to the control and status registers
- Stand-alone mode with preloaded control registers and direct reset input

Figure 2-20. Timer/Counter Block Diagram

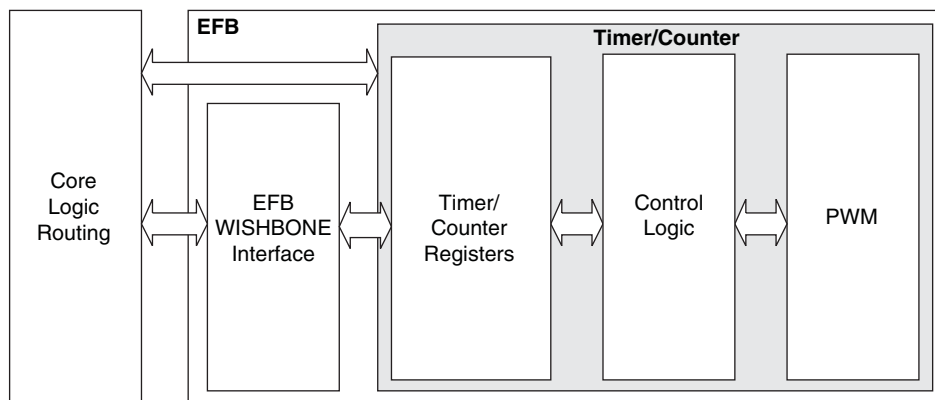


Table 2-16. Timer/Counter Signal Description

Port	I/O	Description
tc_clk	I	Timer/Counter input clock signal
tc_rstn	I	Register tc_rstn_ena is preloaded by configuration to always keep this pin enabled
tc_ic	I	Input capture trigger event, applicable for non-pwm modes with WISHBONE interface. If enabled, a rising edge of this signal will be detected and synchronized to capture tc_cnt value into tc_icr for time-stamping.
tc_int	O	Without WISHBONE – Can be used as overflow flag With WISHBONE – Controlled by three IRQ registers
tc_oc	O	Timer counter output signal

Power-On-Reset Voltage Levels^{1, 2, 3, 4, 5}

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and V_{CCIO0})	0.9	—	1.06	V
$V_{PORUPEXT}$	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	—	2.1	V
$V_{PORDNBG}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CCINT})	0.75	—	0.93	V
$V_{PORDNBGEXT}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	—	1.33	V
$V_{PORDNSRAM}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CCINT})	—	0.6	—	V
$V_{PORDNSRAMEXT}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	—	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.
3. Note that V_{PORUP} (min.) and $V_{PORDNBG}$ (max.) are in different process corners. For any given process corner $V_{PORDNBG}$ (max.) is always 12.0 mV below V_{PORUP} (min.).
4. $V_{PORUPEXT}$ is for C devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.
5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Hot Socketing Specifications^{1, 2, 3}

Symbol	Parameter	Condition	Max.	Units
I_{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/-1000	μA

1. Insensitive to sequence of V_{CC} and V_{CCIO} . However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO} .
2. $0 < V_{CC} < V_{CC}$ (MAX), $0 < V_{CCIO} < V_{CCIO}$ (MAX).
3. I_{DK} is additive to I_{PU} , I_{PD} or I_{BH} .

ESD Performance

Please refer to the [MachXO2 Product Family Qualification Summary](#) for complete qualification data, including ESD performance.

Programming and Erase Supply Current – C/E Devices^{1, 2, 3, 4}

Symbol	Parameter	Device	Typ. ⁴	Units
I_{CC}	Core Power Supply	LCMXO3L/LF-1300C 256 Ball Package	22.1	mA
		LCMXO3L/LF-2100C	22.1	mA
		LCMXO3L/LF-2100C 324 Ball Package	26.8	mA
		LCMXO3L/LF-4300C	26.8	mA
		LCMXO3L/LF-4300C 400 Ball Package	33.2	mA
		LCMXO3L/LF-6900C	33.2	mA
		LCMXO3L/LF-9400C	39.6	mA
		LCMXO3L/LF-640E	17.7	mA
		LCMXO3L/LF-1300E	17.7	mA
		LCMXO3L/LF-1300E 256 Ball Package	18.3	mA
		LCMXO3L/LF-2100E	18.3	mA
		LCMXO3L/LF-2100E 324 Ball Package	20.4	mA
		LCMXO3L/LF-4300E	20.4	mA
		LCMXO3L/LF-6900E	23.9	mA
		LCMXO3L/LF-9400E	28.5	mA
I_{CCIO}	Bank Power Supply ⁵ VCCIO = 2.5 V	All devices	0	mA

1. For further information on supply current, please refer to TN1289, [Power Estimation and Management for MachXO3 Devices](#).

2. Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.

3. Typical user pattern.

4. JTAG programming is at 25 MHz.

5. T_J = 25 °C, power supplies at nominal voltage.

6. Per bank. V_{CCIO} = 2.5 V. Does not include pull-up/pull-down.

Table 3-5. MIPI D-PHY Output DC Conditions¹

	Description	Min.	Typ.	Max.	Units
Transmitter					
External Termination					
RL	1% external resistor with VCCIO = 2.5 V	—	50	—	Ohms
	1% external resistor with VCCIO = 3.3 V	—	50	—	
RH	1% external resistor with performance up to 800 Mbps or with performance up 900 Mbps when VCCIO = 2.5 V	—	330	—	Ohms
	1% external resistor with performance between 800 Mbps to 900 Mbps when VCCIO = 3.3 V	—	464	—	Ohms
High Speed					
VCCIO	VCCIO of the Bank with LVDS Emulated output buffer	—	2.5	—	V
	VCCIO of the Bank with LVDS Emulated output buffer	—	3.3	—	V
VCMTX	HS transmit static common mode voltage	150	200	250	mV
VOD	HS transmit differential voltage	140	200	270	mV
VOHHS	HS output high voltage	—	—	360	V
ZOS	Single ended output impedance	—	50	—	Ohms
ΔZOS	Single ended output impedance mismatch	—	—	10	%
Low Power					
VCCIO	VCCIO of the Bank with LVCMOS12D 6 mA drive bidirectional IO buffer	—	1.2	—	V
VOH	Output high level	1.1	1.2	1.3	V
VOL	Output low level	–50	0	50	mV
ZOLP	Output impedance of LP transmitter	110	—	—	Ohms

¹. Over Recommended Operating Conditions

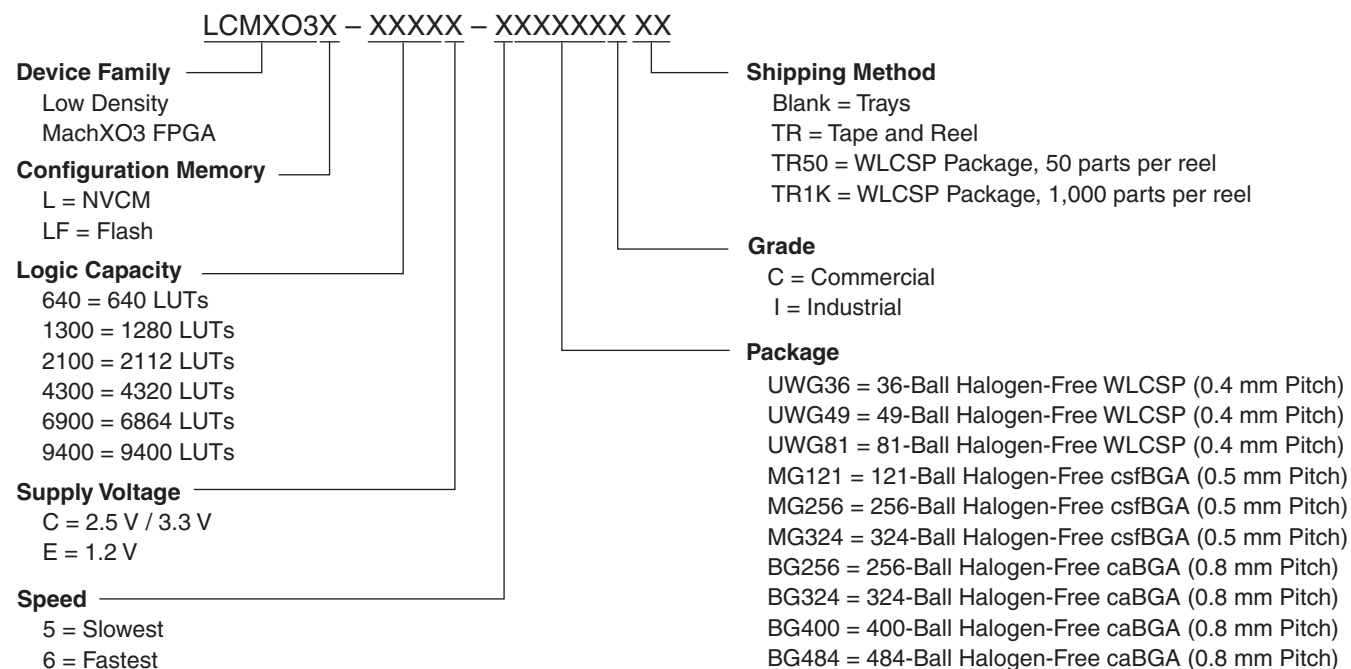
Parameter	Description	Device	-6		-5		Units
			Min.	Max.	Min.	Max.	
Generic DDRX4 Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDR ₄ _TX.ECLK.Centered ^{8, 9}							
t _{DVB}	Output Data Valid Before CLK Output	MachXO3L/LF devices, top side only	0.455	—	0.570	—	ns
t _{DVA}	Output Data Valid After CLK Output		0.455	—	0.570	—	ns
f _{DATA}	DDRX4 Serial Output Data Speed		—	800	—	630	Mbps
f _{DDRX4}	DDRX4 ECLK Frequency (minimum limited by PLL)		—	400	—	315	MHz
f _{SCLK}	SCLK Frequency		—	100	—	79	MHz
7:1 LVDS Outputs – GDDR ₇₁ _TX.ECLK.7:1 ^{8, 9}							
t _{DIB}	Output Data Invalid Before CLK Output	MachXO3L/LF devices, top side only	—	0.160	—	0.180	ns
t _{DIA}	Output Data Invalid After CLK Output		—	0.160	—	0.180	ns
f _{DATA}	DDR71 Serial Output Data Speed		—	756	—	630	Mbps
f _{DDR71}	DDR71 ECLK Frequency		—	378	—	315	MHz
f _{CLKOUT}	7:1 Output Clock Frequency (SCLK) (minimum limited by PLL)		—	108	—	90	MHz
MIPI D-PHY Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input - GDDR ₄ _TX.ECLK.Centered ^{10, 11, 12}							
t _{DVB}	Output Data Valid Before CLK Output	All MachXO3L/LF devices, top side only	0.200	—	0.200	—	UI
t _{DVA}	Output Data Valid After CLK Output		0.200	—	0.200	—	UI
f _{DATA} ¹⁴	MIPI D-PHY Output Data Speed		—	900	—	900	Mbps
f _{DDRX4} ¹⁴	MIPI D-PHY ECLK Frequency (minimum limited by PLL)		—	450	—	450	MHz
f _{SCLK} ¹⁴	SCLK Frequency		—	112.5	—	112.5	MHz

- Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
- General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0pF load, fast slew rate.
- Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
- 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
- For Generic DDRX1 mode t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03 ns)/2.
- The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 105 ps (-6), 113 ps (-5), 120 ps (-4).
- This number for general purpose usage. Duty cycle tolerance is +/-10%.
- Duty cycle is +/- 5% for system usage.
- Performance is calculated with 0.225 UI.
- Performance is calculated with 0.20 UI.
- Performance for Industrial devices are only supported with VCC between 1.16 V to 1.24 V.
- Performance for Industrial devices and -5 devices are not modeled in the Diamond design tool.
- The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
- Above 800 Mbps is only supported with WLCSP and csfBGA packages
- Between 800 Mbps to 900 Mbps:
 - VIDTH exceeds the MIPI D-PHY Input DC Conditions Table 3-4 and can be calculated with the equation t_{SU} or t_H = -0.0005*VIDTH + 0.3284
 - Example calculations
 - t_{SU} and t_{HO} = 0.28 with VIDTH = 100 mV
 - t_{SU} and t_{HO} = 0.25 with VIDTH = 170 mV
 - t_{SU} and t_{HO} = 0.20 with VIDTH = 270 mV

Pin Information Summary

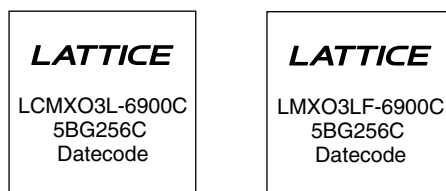
	MachXO3L/LF-640	MachXO3L/LF-1300			
	CSFBGA121	WLCSP36	CSFBGA121	CSFBGA256	CABGA256
General Purpose IO per Bank					
Bank 0	24	15	24	50	50
Bank 1	26	0	26	52	52
Bank 2	26	9	26	52	52
Bank 3	24	4	24	16	16
Bank 4	0	0	0	16	16
Bank 5	0	0	0	20	20
Total General Purpose Single Ended IO	100	28	100	206	206
Differential IO per Bank					
Bank 0	12	8	12	25	25
Bank 1	13	0	13	26	26
Bank 2	13	4	13	26	26
Bank 3	11	2	11	8	8
Bank 4	0	0	0	8	8
Bank 5	0	0	0	10	10
Total General Purpose Differential IO	49	14	49	103	103
Dual Function IO	33	25	33	33	33
Number 7:1 or 8:1 Gearboxes					
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	7	3	7	14	14
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	7	2	7	14	14
High-speed Differential Outputs					
Bank 0	7	3	7	14	14
VCCIO Pins					
Bank 0	1	1	1	4	4
Bank 1	1	0	1	3	4
Bank 2	1	1	1	4	4
Bank 3	3	1	3	2	1
Bank 4	0	0	0	2	2
Bank 5	0	0	0	2	1
VCC	4	2	4	8	8
GND	10	2	10	24	24
NC	0	0	0	0	1
Reserved for Configuration	1	1	1	1	1
Total Count of Bonded Pins	121	36	121	256	256

MachXO3 Part Number Description



Ordering Information

MachXO3L/LF devices have top-side markings as shown in the examples below, on the 256-Ball caBGA package with MachXO3-6900 device in Commercial Temperature in Speed Grade 5. Notice that for the MachXO3LF device, *LMXO3LF* is used instead of *LCMXO3LF* as in the Part Number.



Note: *LCMXO3LF* is marked with *LMXO3LF*

Note: Markings are abbreviated for small packages.

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-2100E-6MG324I	2100	1.2 V	6	Halogen-Free csfBGA	324	IND
LCMXO3L-2100C-5BG256C	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3L-2100C-6BG256C	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3L-2100C-5BG256I	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3L-2100C-6BG256I	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3L-2100C-5BG324C	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	COM
LCMXO3L-2100C-6BG324C	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	COM
LCMXO3L-2100C-5BG324I	2100	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	IND
LCMXO3L-2100C-6BG324I	2100	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-4300E-5UWG81CTR	4300	1.2 V	5	Halogen-Free WLCSP	81	COM
LCMXO3L-4300E-5UWG81CTR50	4300	1.2 V	5	Halogen-Free WLCSP	81	COM
LCMXO3L-4300E-5UWG81CTR1K	4300	1.2 V	5	Halogen-Free WLCSP	81	COM
LCMXO3L-4300E-5UWG81ITR	4300	1.2 V	5	Halogen-Free WLCSP	81	IND
LCMXO3L-4300E-5UWG81ITR50	4300	1.2 V	5	Halogen-Free WLCSP	81	IND
LCMXO3L-4300E-5UWG81ITR1K	4300	1.2 V	5	Halogen-Free WLCSP	81	IND
LCMXO3L-4300E-5MG121C	4300	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3L-4300E-6MG121C	4300	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3L-4300E-5MG121I	4300	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3L-4300E-6MG121I	4300	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3L-4300E-5MG256C	4300	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3L-4300E-6MG256C	4300	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3L-4300E-5MG256I	4300	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3L-4300E-6MG256I	4300	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3L-4300E-5MG324C	4300	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3L-4300E-6MG324C	4300	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3L-4300E-5MG324I	4300	1.2 V	5	Halogen-Free csfBGA	324	IND
LCMXO3L-4300E-6MG324I	4300	1.2 V	6	Halogen-Free csfBGA	324	IND
LCMXO3L-4300C-5BG256C	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3L-4300C-6BG256C	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3L-4300C-5BG256I	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3L-4300C-6BG256I	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3L-4300C-5BG324C	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	COM
LCMXO3L-4300C-6BG324C	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	COM
LCMXO3L-4300C-5BG324I	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	IND
LCMXO3L-4300C-6BG324I	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	IND
LCMXO3L-4300C-5BG400C	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	COM
LCMXO3L-4300C-6BG400C	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	COM
LCMXO3L-4300C-5BG400I	4300	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	IND
LCMXO3L-4300C-6BG400I	4300	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	IND

MachXO3 Family Data Sheet

Revision History

February 2017

Advance Data Sheet DS1047

Date	Version	Section	Change Summary
February 2017	1.8	Architecture	Updated Supported Standards section. Corrected “MDVS” to “MLDVS” in Table 2-11, Supported Input Standards.
		DC and Switching Characteristics	Updated ESD Performance section. Added reference to the MachXO2 Product Family Qualification Summary document.
			Updated Static Supply Current – C/E Devices section. Added footnote 7.
			Updated MachXO3L/LF External Switching Characteristics – C/E Devices section. — Populated values for MachXO3L/LF-9400. — Under 7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1, corrected “t _{DVB} ” to “t _{DIB} ” and “t _{DVA} ” to “t _{DIA} ” and revised their descriptions. — Added Figure 3-6, Receiver GDDR71_RX Waveforms and Figure 3-7, Transmitter GDDR71_TX Waveforms.
		Pinout Information	Updated the Pin Information Summary section. Added MachXO3L/LF-9600C packages.
May 2016	1.7	DC and Switching Characteristics	Updated Absolute Maximum Ratings section. Modified I/O Tri-state Voltage Applied and Dedicated Input Voltage Applied footnotes.
			Updated sysIO Recommended Operating Conditions section. — Added standards. — Added V _{REF} (V) — Added footnote 4.
			Updated sysIO Single-Ended DC Electrical Characteristics section. Added I/O standards.
		Ordering Information	Updated MachXO3L Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.
			Updated MachXO3LF Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added LCMXO3L-9400C part numbers.

Date	Version	Section	Change Summary
June 2014	1.0	—	Product name/trademark adjustment.
		Introduction	Updated Features section.
			Updated Table 1-1, MachXO3L Family Selection Guide. Changed fcCSP packages to csfBGA. Adjusted 121-ball csfBGA arrow.
			Introduction section general update.
		Architecture	General update.
		DC and Switching Characteristics	Updated sysIO Recommended Operating Conditions section. Removed V_{REF} (V) column. Added standards.
			Updated Maximum sysIO Buffer Performance section. Added MIPI I/O standard.
			Updated MIPI D-PHY Emulation section. Changed Low Speed to Low Power. Updated Table 3-4, MIPI DC Conditions.
			Updated Table 3-5, MIPI D-PHY Output DC Conditions.
			Updated Maximum sysIO Buffer Performance section.
			Updated MachXO3L External Switching Characteristics – C/E Device section.
May 2014	00.3	Introduction	Updated Features section.
			Updated Table 1-1, MachXO3L Family Selection Guide. Moved 121-ball fcCSP arrow.
			General update of Introduction section.
		Architecture	General update.
		Pinout Information	Updated Pin Information Summary section. Updated or added data on WLCSP49, WLCSP81, CABGA324, and CABGA400 for specific devices.
		Ordering Information	Updated MachXO3L Part Number Description section. Updated or added data on WLCSP49, WLCSP81, CABGA324, and CABGA400 for specific devices.
			Updated Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging section. Added part numbers.
February 2014	00.2	DC and Switching Characteristics	Updated MachXO3L External Switching Characteristics – C/E Devices table. Removed LPDDR and DDR2 parameters.
	00.1	—	Initial release.